Space environment: effect on detectors examples with Integral and Astro-H

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Description of the space environment.
 Effect of radiation on electronic devices.
 Calibration project for Astro-H.

The space environment

Space constraints

> Launch

- Chocks, vibrations
- Space environment
 - Thermal Variations
 - Vacuum
 - Radiations
 - Contamination
 - Micrometeorites, space debris

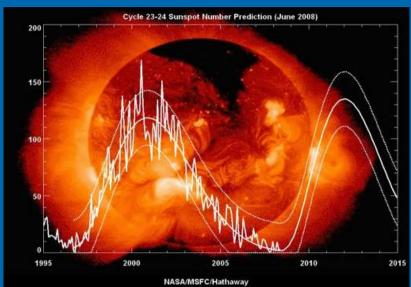
The radiative environment

Solar activity

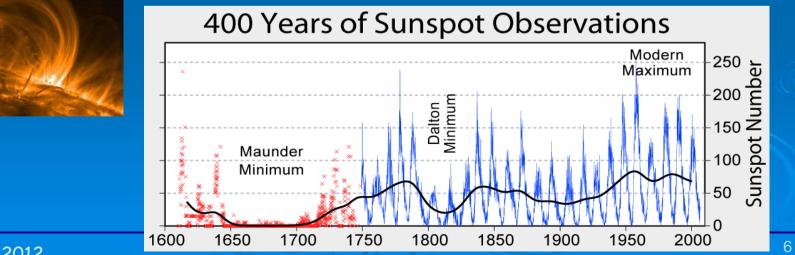
Sunspot (Galilée, 1610)



flares

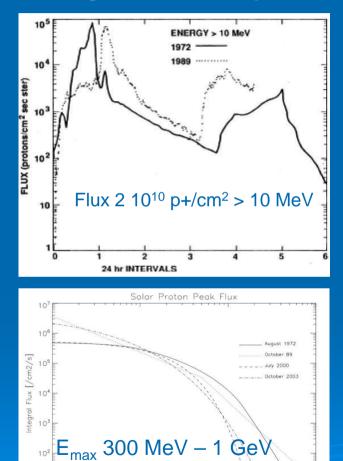


11 ± 2 years cycle Cycles are not similar !



Solar particles

Events occuring on hours to days timescale

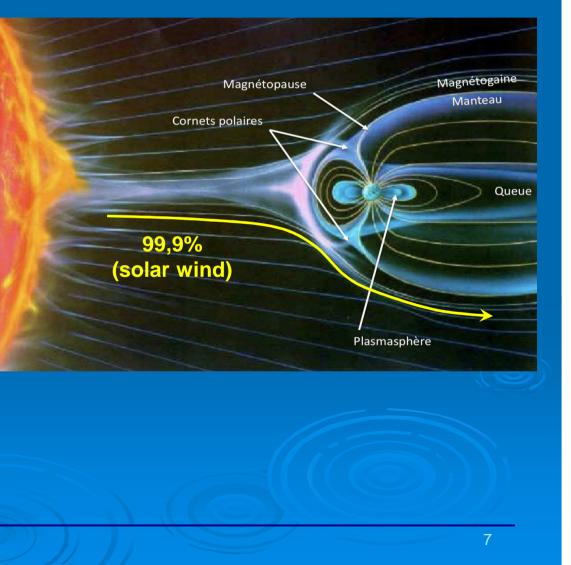


10

Energy [MeV]

100

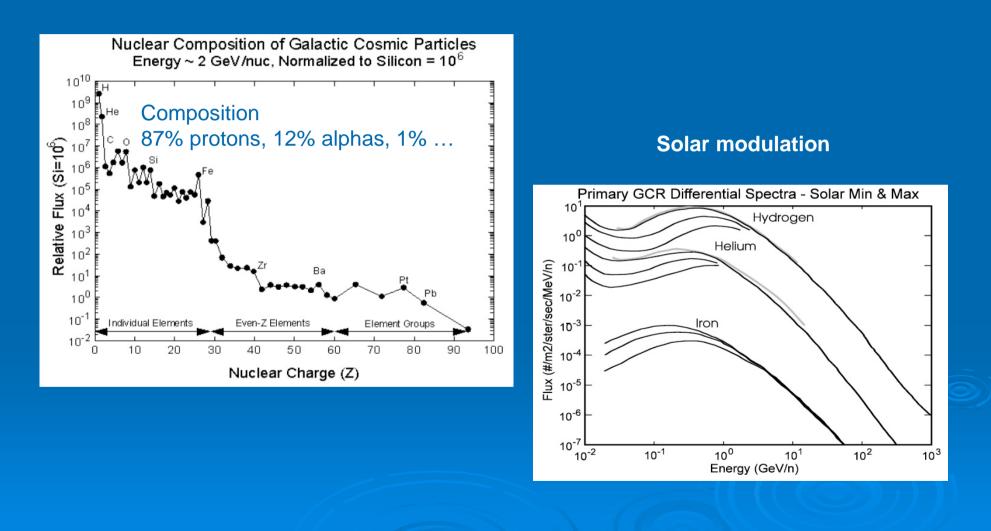
1000



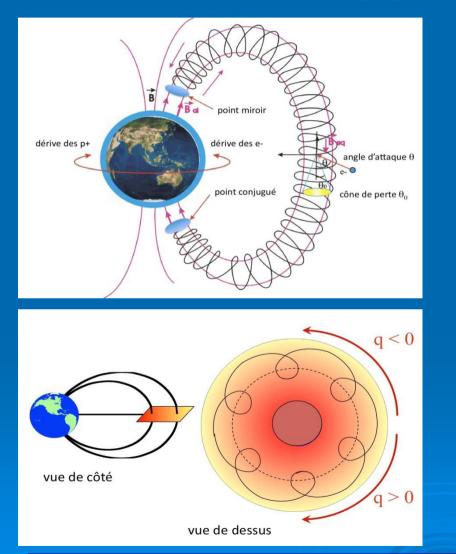
November, 9th 2012

10

Cosmic Rays

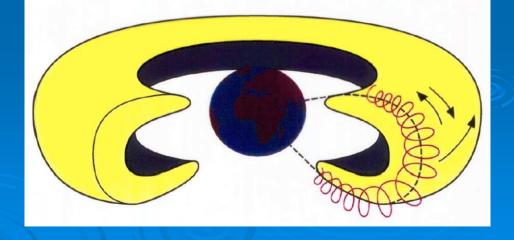


Trapped particles



Trapping mechanisms:

- rotation (Lorentz force)
- Magnetic mirror.
- East-West drift, due to magnetic field gradient.



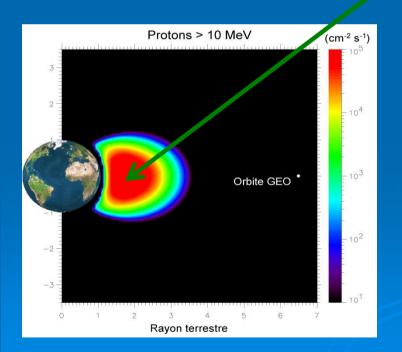
Van Allen belts

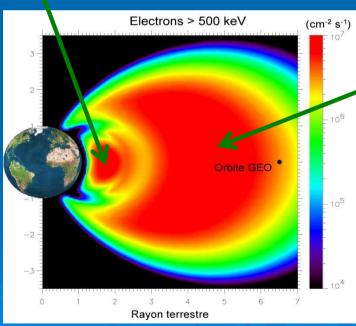
Two belts:

- Internal (stable)
- External (dynamic)

Protons and electrons coming from cosmic and solar particles interaction into the atmosphere

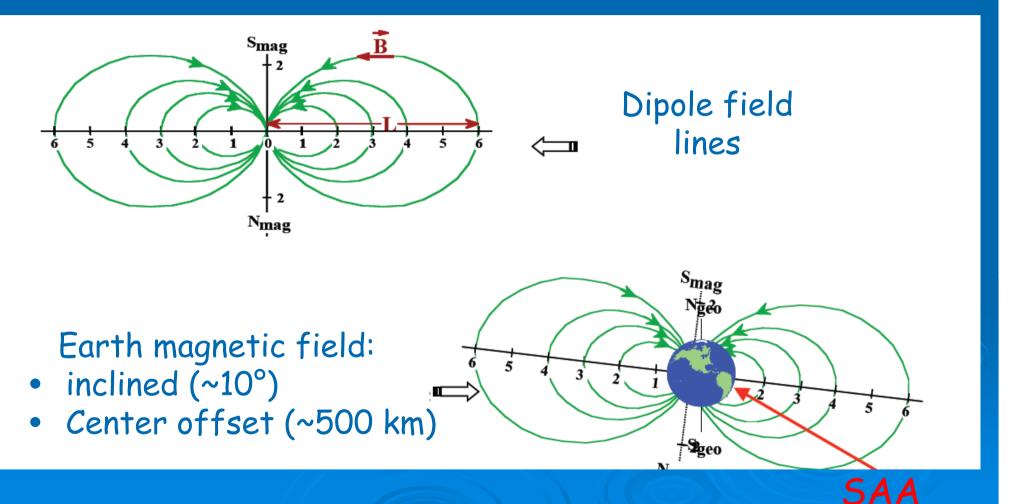
 $n \rightarrow p^{\dagger} + e^{\dagger} + v_{e}$





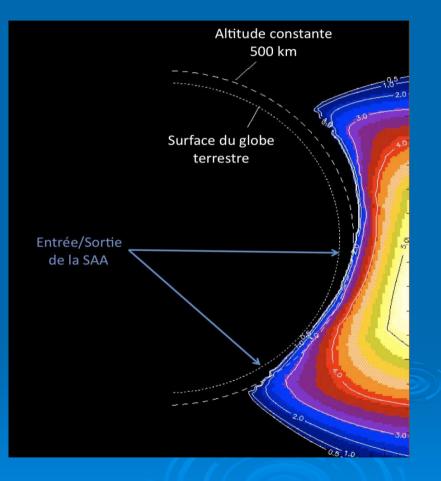
Solar particles injected from the magnetosphere tail.

South Atlantic Anomaly (1/2)



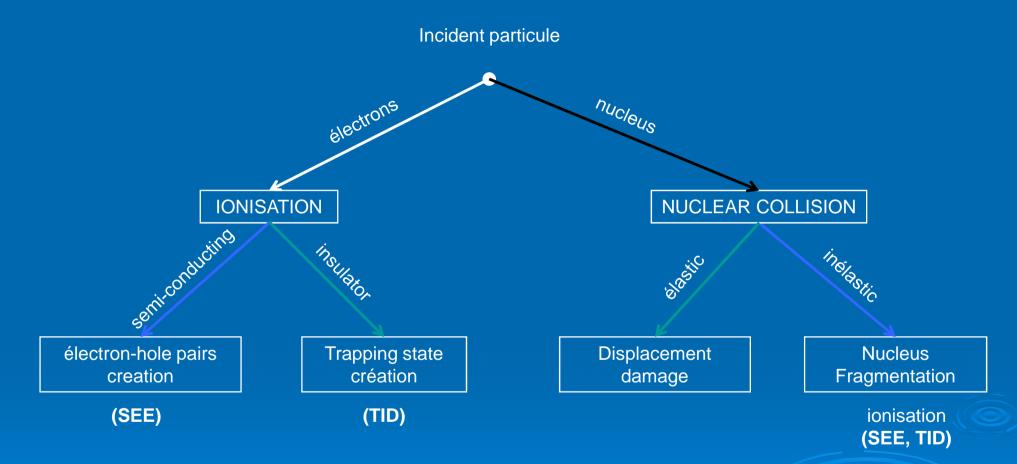
South Atlantic Anomaly (2/2)

- The South Atlantic Anomaly (SAA) is an area where the Earth's inner Van Allen radiation belt comes closest to the Earth's.
- This leads to an increased flux of energetic particles in this region.
- The effect is caused by the nonconcentricity of the Earth and its magnetic dipole.



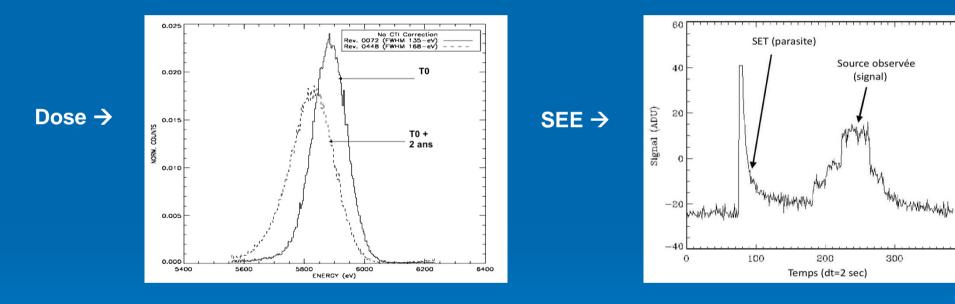
Effect of radiations on electronic devices

Effects on electronic devices



TID : "Total Ionising Dose" is a long cumulative effect
SEE : "Single Event Effect" is a transient single effect

Examples



Spectral resolution dégradation (XMM)

Transient signal (ISOCAM)

November, 9th 2012

400

Effect of SEE on electronic devices

Effect of the ionizing particle depends on the energy deposit in the component (LET):

$$LET = \frac{1}{\rho} \frac{dE}{dx}$$

- Latch-up (SEL) : parasitic current induce by the particle passage which could produce a short-circuit and potentially destroy the component.
- > Single event upset (SEU): bit flip in a register.
- Radhard Technics to immunize the electronics against SEE.

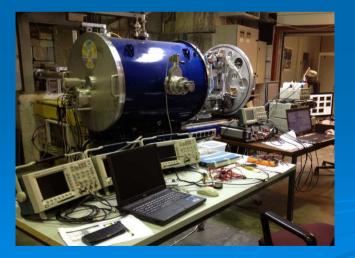
Component tolerance to SEE (1/3)

Measures of the circuit properties

SEL and SEU (*single event latch-up / upset*) cross sections with respect to LET (*linear energy transfer*) :

$$\sigma = \frac{N_{LET}}{N_{inc}}$$

 N_{inc} = number of incident ions which will depose a given LET.



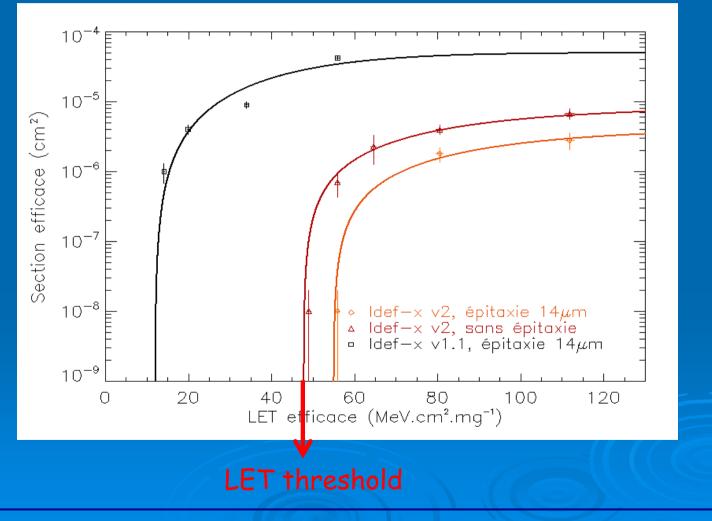
M/Q = 3,33			
Ion	Energy	LET	Range
1011	[MeV]	[MeV/mg/cm2]	[microns]
¹³ C ⁺⁴	131	1.2	266
²² Ne ⁺⁷	235	3.6	199
⁴⁰ Ar ⁺¹²	372	9.95	119
⁵⁸ Ni ⁺¹⁸	567	21.3	98
⁸³ Kr ⁺²⁵	756	31.0	92

M/Q = 5

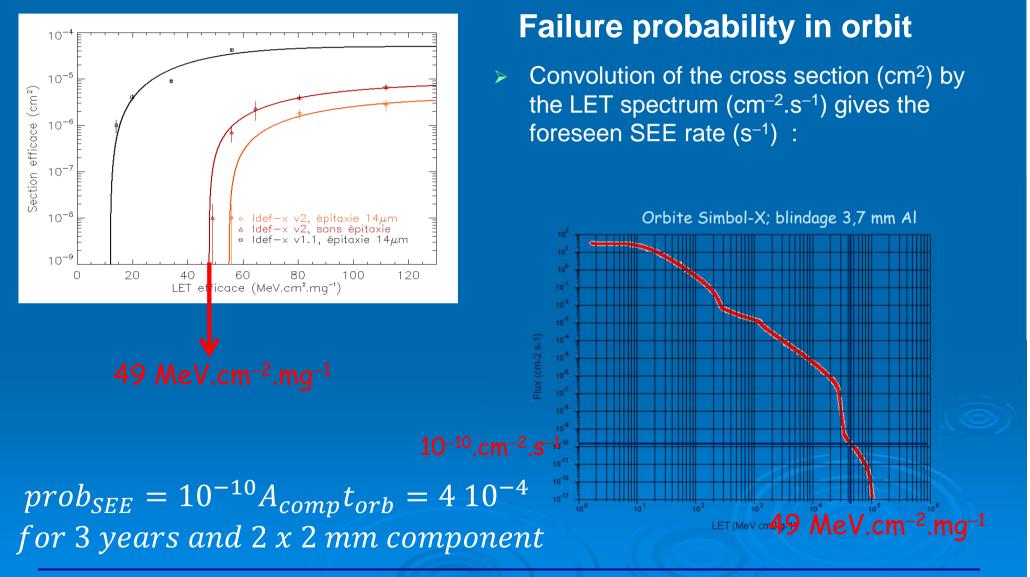
Ion	Energy	LET	Range
Ion	[MeV]	[MeV/mg/cm2]	[microns]
$^{15}N^{+3}$	62	3.3	64
²⁰ Ne ⁺⁴	78	6.2	45
40 Ar+8	150	15.9	42
⁸⁴ Kr ⁺¹⁷	316	40.1	43
$^{132}\mathrm{Xe}^{+26}$	459	67.7	43

Component tolerance to SEE (2/3)

Measures of the circuit properties



Component tolerance to SEE (3/3)



Calibration project for Astro-H

Context: ESA contribution to Astro-H

ESA CONTRIBUTION TO	Doc. no. :SRON-ASTH-PL-2010-004 Issue :2.2
ASTRO-H	Date : 26 September 2010 Page : 2 of 36

ESA contribution to the Japanese X-ray mission ASTRO-H

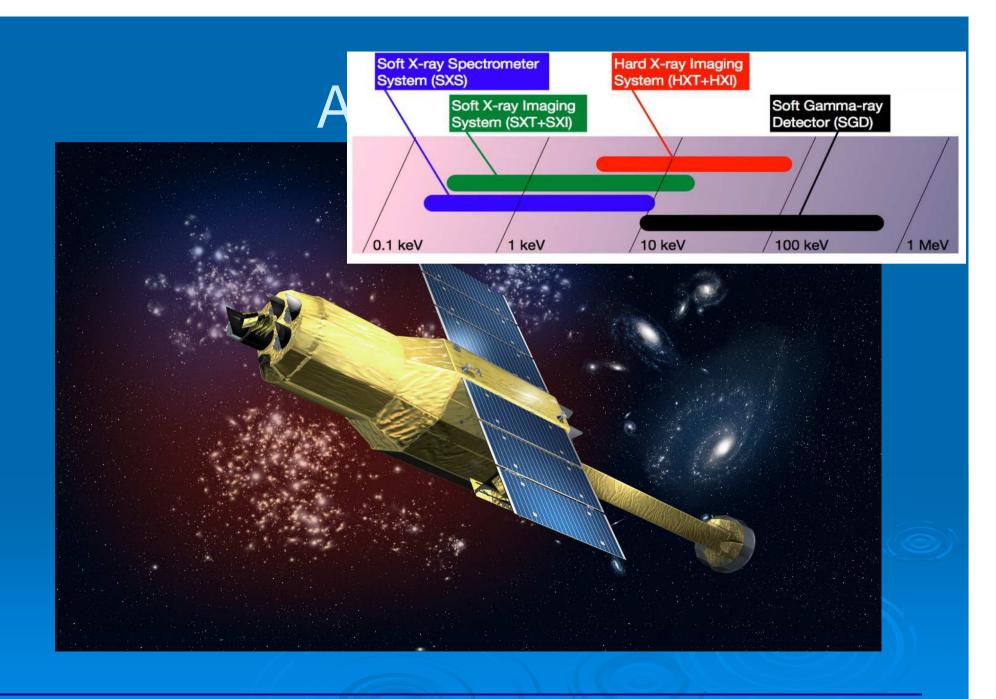
Technical lead:

Dr. J.W. den Herder (proposal leader)	Dr. P Laurent	
SRON, the Netherlands Institute for Space	CEA/DSM/IRFU/SAp	
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e-mail: J.den.Herder@sron.nl	e-mail: Philippe.Laurent@cea.fr	

Context

ASTRO-H is the next major X-ray mission with a planned launch date of 2014. Its key scientific objectives include:

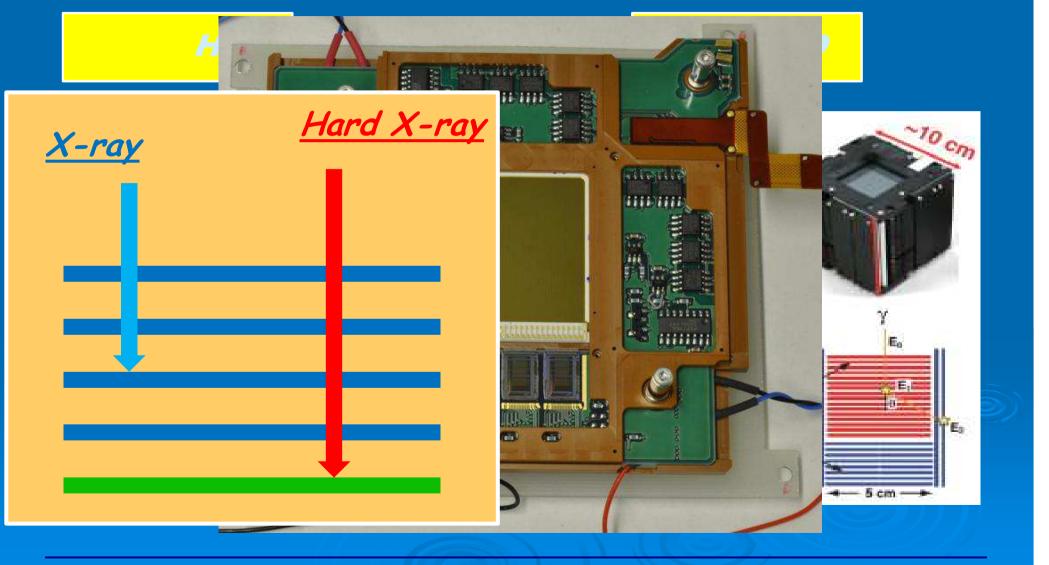
- revealing the large scale structure of the Universe and its evolution



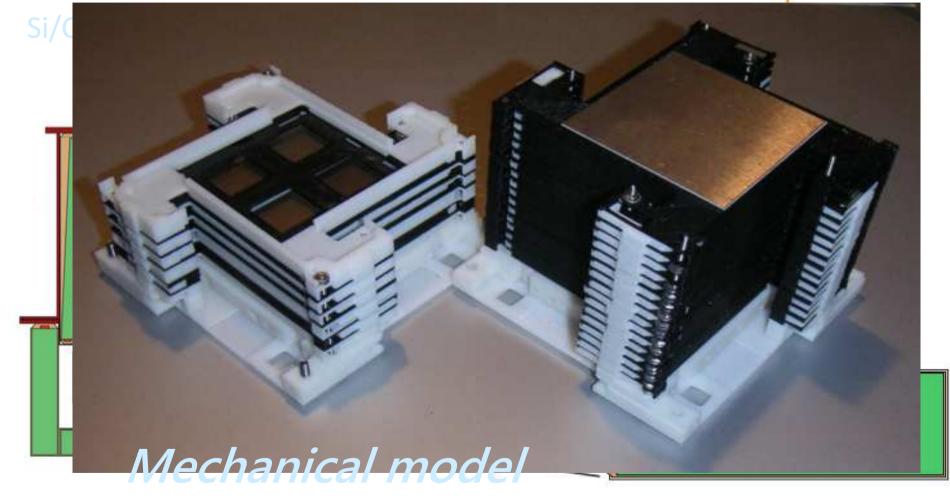
ASTRO-H



HXI and SGD



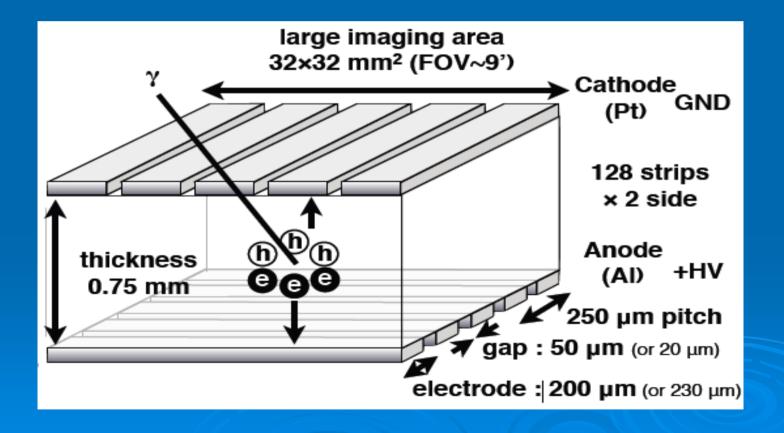
HXI and SGD





Detector for HXI

DS-CdTe : high detection efficiency thanks its atomic number (48-52)

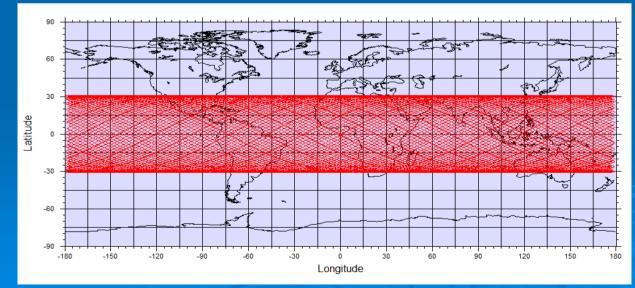


Study of Astro-H SGD ASICs

Astro-H orbit

Low Earth Orbit

- Orbit Altitude: 550 km
- Orbit Inclination: ~31 degrees
- Orbit Period: 96 minutes
- Launch : 2014
- > 4 years of operation



Models used to determine the Astro-H space environment

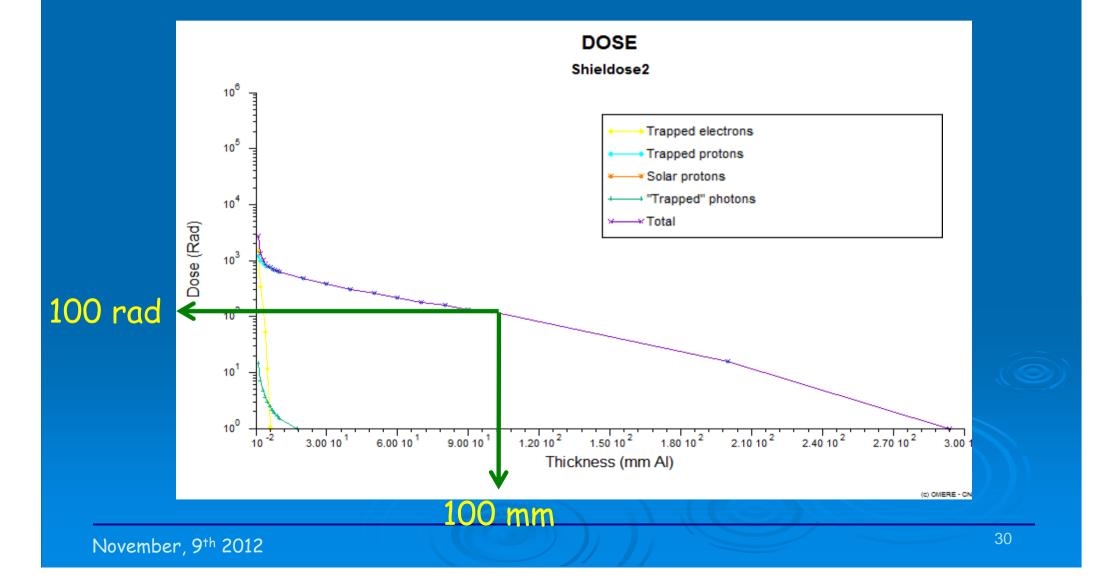
a) Trapped protons model is AP-8 MAX (NASA/NSSDC)

b) Trapped electrons model is AE-8 MIN (NASA/NSSDC)

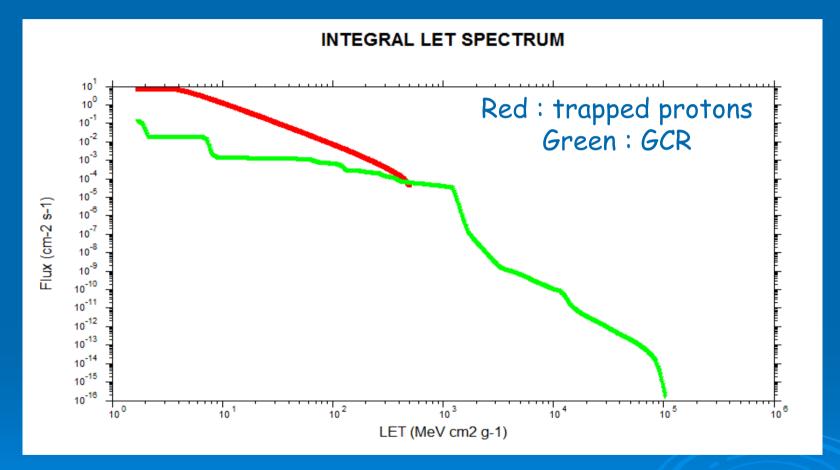
c) Solar protons model is SOLPRO (NASA/NSSDC)

d) Cosmic-ray model is GCR-ISO (ISO 15390)

Dose curve

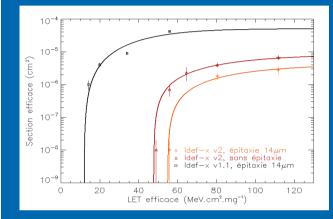


LET spectrum



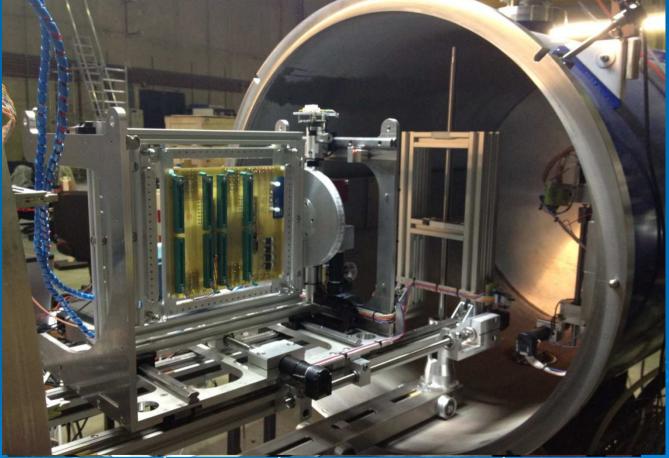
LET computed with 10 cm Al shielding

Radiation Test (1/2)



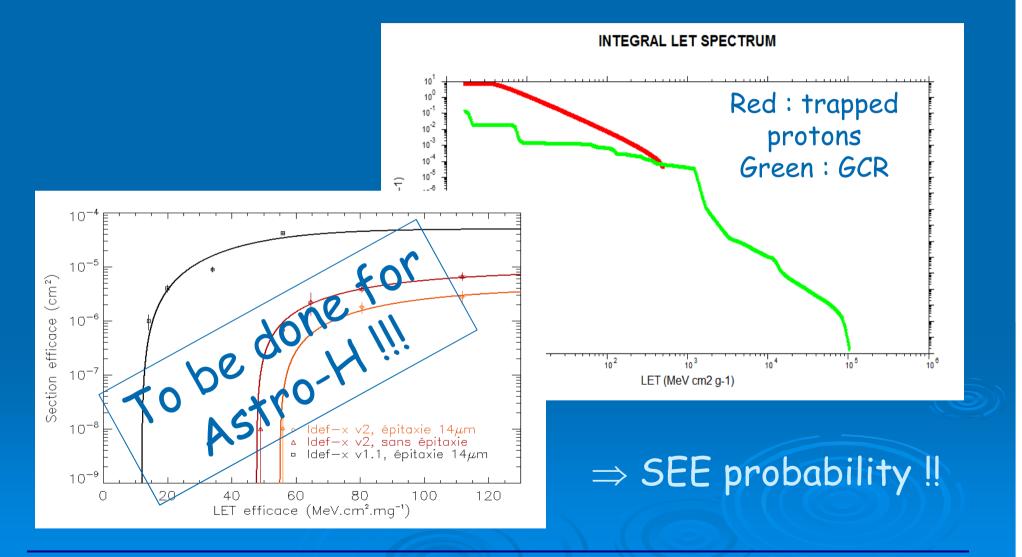
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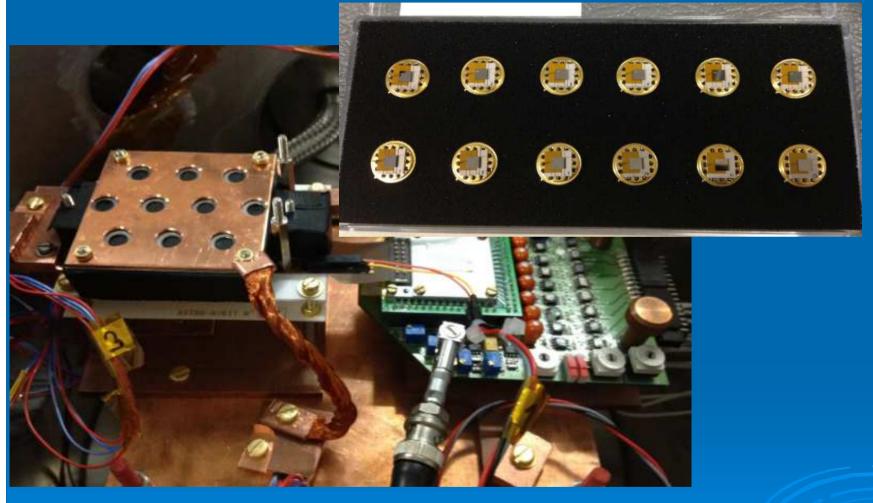
HIF accelerator line at Louvain-la-Neuve (Belgium)

Radiation tests (2/2)

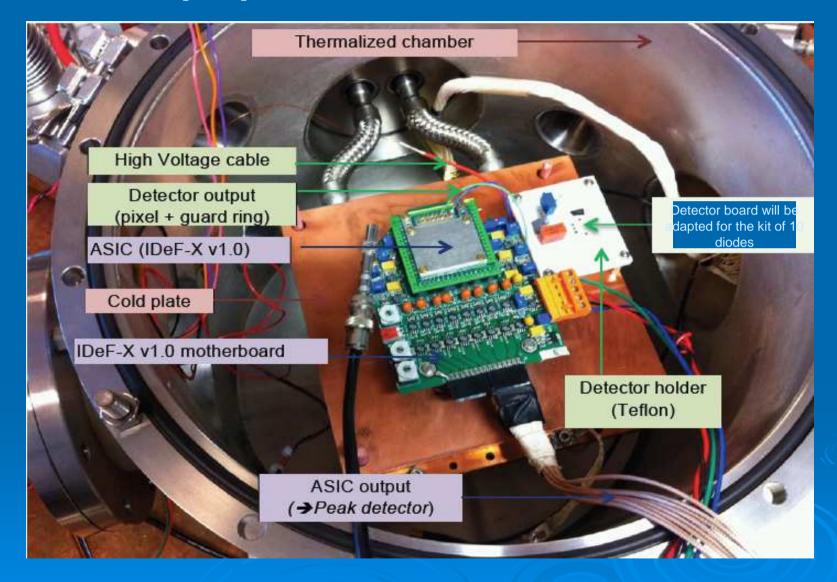


Study of Astro-H HXI and SGD CdTe detectors

Test bench in CEA



test equipment for the diodes



PSI protons accelerator (Switzerland)



Thank you !